(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau

(43) International Publication Date
9 February 2012 (09.02.2012)

PCT

(10) International Publication Number
WO 2012/018368 A2

(51) **International Patent Classification**:
H05H 1/24 (2006.01) ***H01L 21/3065*** (2006.01)
H01L 21/205 (2006.01)

(21) **International Application Number**:
PCT/US2011/001270

(22) **International Filing Date**:
18 July 2011 (18.07.2011)

(25) **Filing Language**: English

(26) **Publication Language**: English

(30) **Priority Data**:
12/844,527 27 July 2010 (27.07.2010) US

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(81) **Designated States** *(unless otherwise indicated, for every kind of national protection available)*: AE, AG, AL, AM, AO, AT, AU, AZ, BA, BB, BG, BH, BR, BW, BY, BZ, CA, CH, CL, CN, CO, CR, CU, CZ, DE, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IS, JP, KE, KG, KM, KN, KP, KR, KZ, LA, LC, LK, LR, LS, LT, LU, LY, MA, MD, ME, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PE, PG, PH, PL, PT, RO, RS, RU, SC, SD, SE, SG, SK, SL, SM, ST, SV, SY, TH, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW.

(84) **Designated States** *(unless otherwise indicated, for every kind of regional protection available)*: ARIPO (BW, GH, GM, KE, LR, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AL, AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV, MC, MK, MT, NL, NO, PL, PT, RO, RS, SE, SI, SK, SM, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Declarations under Rule 4.17:

— *as to applicant's entitlement to apply for and be granted a patent (Rule 4.17(ii))*

[Continued on next page]

(54) **Title**: PARASITIC PLASMA PREVENTION IN PLASMA PROCESSING CHAMBERS

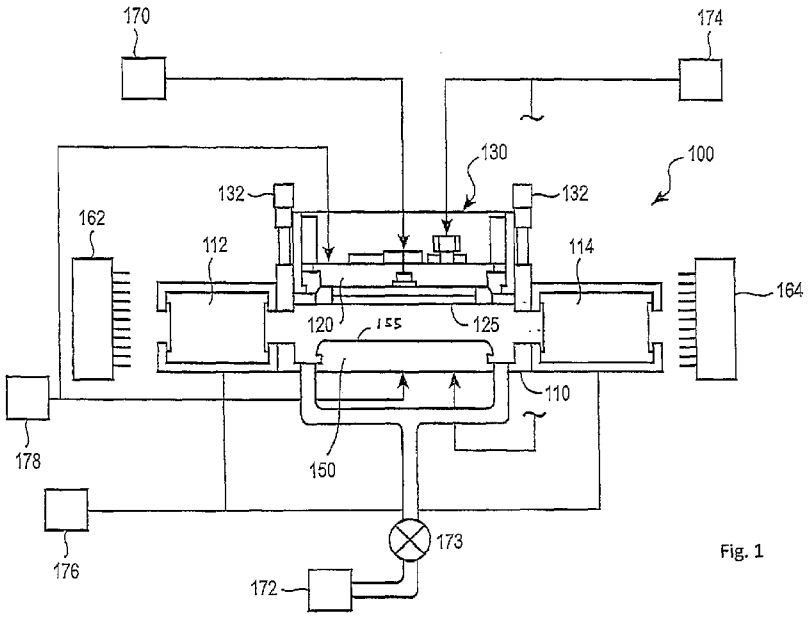


Fig. 1

(57) **Abstract**: Parasitic plasma in voids in a component of a plasma processing chamber can be eliminated by covering electrically conductive surfaces in an interior of the voids with a sleeve. The voids can be gas holes, lift pin holes, helium passages, conduits and/or plenums in chamber components such as an upper electrode and a substrate support.

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— *as to the applicant's entitlement to claim the priority of the earlier application (Rule 4.17(iii))*

Published:

— *without international search report and to be republished upon receipt of that report (Rule 48.2(g))*